Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	3.0 2.5	A
Pulsed Drain Current (10µs pulse, Duty cycle = 1%)			I_{DM}	10	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	0.6	W
	(Note 6)		1.8	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	200	°C/W
	(Note 6)		67	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics N-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	67	85	mΩ	V_{GS} = 10V, I_D = 1.5A
			74	120		V_{GS} = 4V, I_D = 0.5A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	2.6	—	S	V_{DS} = 5V, I_D = 1.5A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 3A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	606	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	32.6	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	24.6	—	pF	
Gate Resistance	R_g	—	1.5	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} =10V)	Q_g	—	12.3	—	nC	V_{DS} = 30V, I_D = 3A
Total Gate Charge (V_{GS} =4.5V)	Q_g	—	5.6	—	nC	
Gate-Source Charge	Q_{gs}	—	1.7	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.9	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	3.5	—	ns	V_{GS} = 10V, V_{DS} = 30V, R_G = 20Ω, R_L = 50Ω
Turn-On Rise Time	t_r	—	4.1	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	35	—	ns	
Turn-Off Fall Time	t_f	—	11	—	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

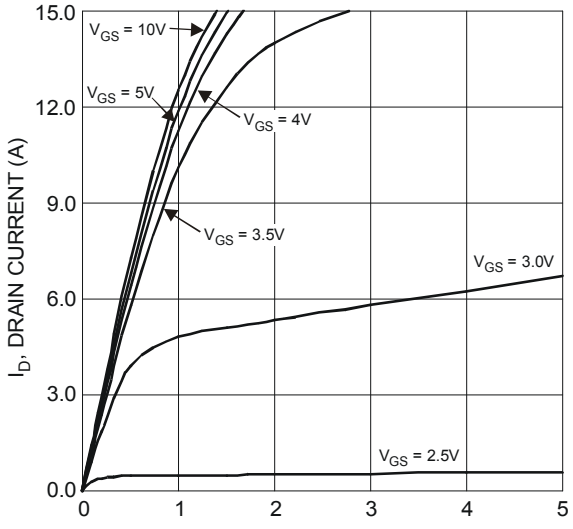


Figure 1 Typical Output Characteristics

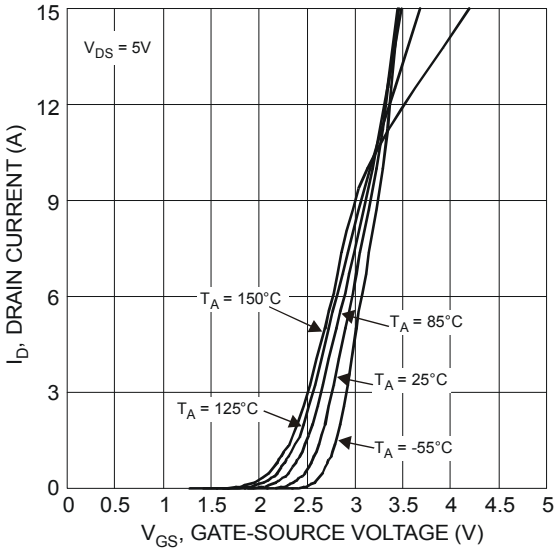


Figure 2 Typical Transfer Characteristics

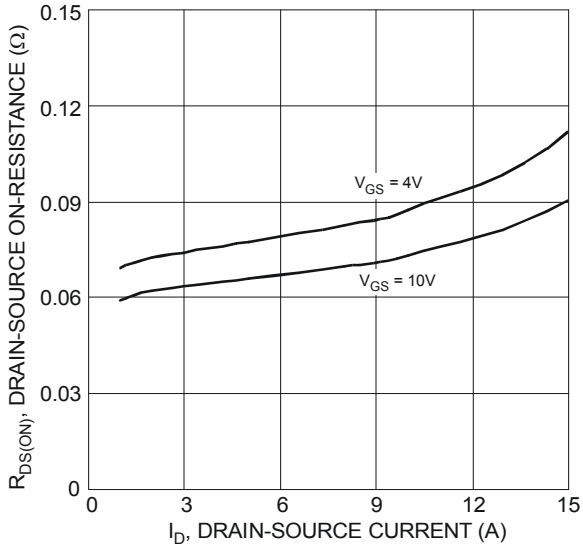


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

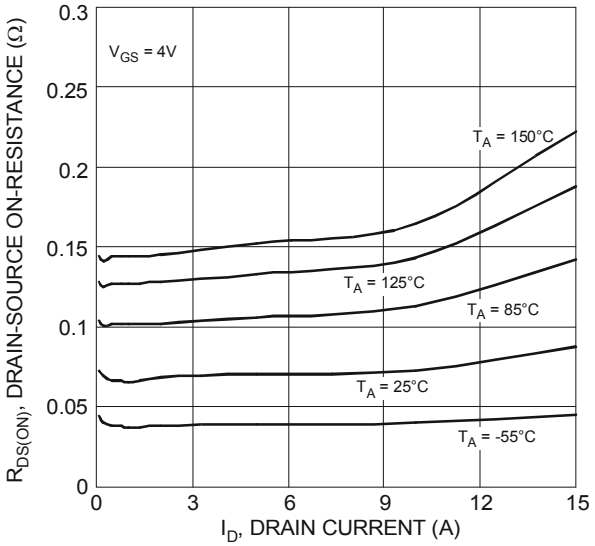


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

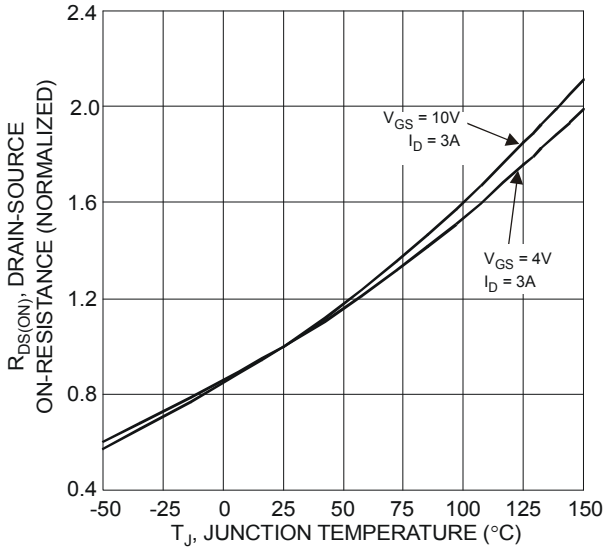


Figure 5 On-Resistance Variation with Temperature

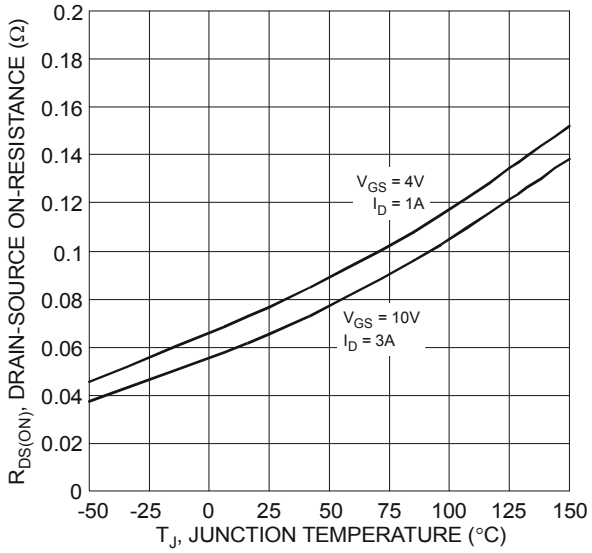


Figure 6 On-Resistance Variation with Temperature

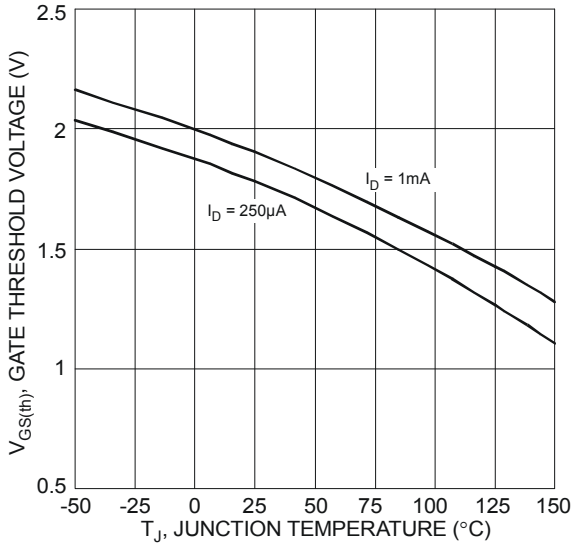


Figure 7 Gate Threshold Variation vs. Ambient Temperature

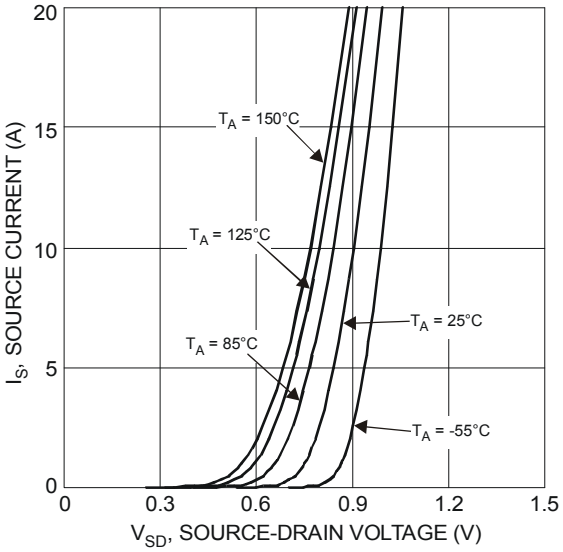


Figure 8 Diode Forward Voltage vs. Current

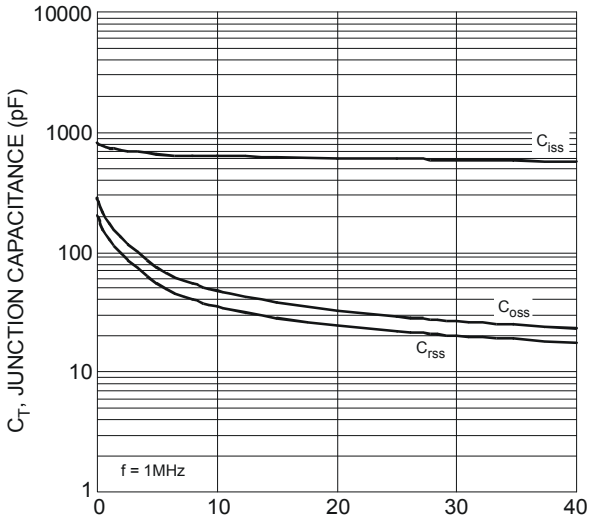


Figure 9 Typical Junction Capacitance

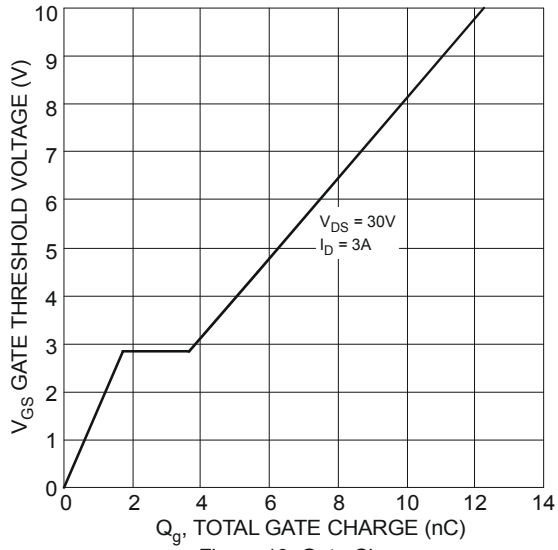
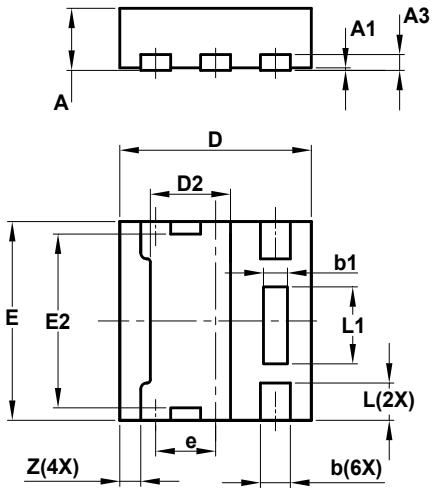


Figure 10 Gate Charge

Package Outline Dimensions

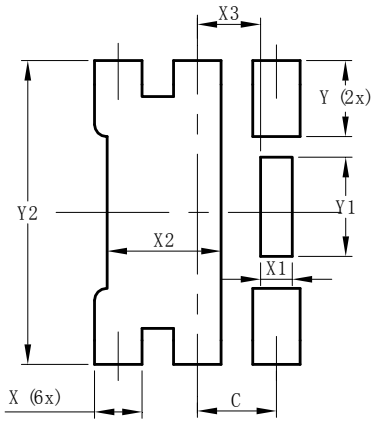
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



X1-DFN1616-6 Type E			
Dim	**Min**	**Max**	**Typ**
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
b1	0.10	0.30	0.20
D	1.55	1.65	1.60
D2	0.57	0.77	0.67
E	1.55	1.65	1.60
E2	1.30	1.50	1.40
e	—	—	0.50
L	0.25	0.35	0.30
L1	0.52	0.72	0.62
Z	—	—	0.175
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
C	0.500
X	0.300
X1	0.200
X2	0.720
X3	0.400
Y	0.475
Y1	0.620
Y2	1.900